

L Number	Hits	Search Text	DB	Time stamp
1	5	"6537844"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 12:16
2	9429	high adj breakdown	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 12:17
3	2395	low adj breakdown	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 12:17
4	914	(high adj breakdown) and (low adj breakdown)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 12:17
5	240	((high adj breakdown) and (low adj breakdown)) and mosfet	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 12:18
6	310621	impurities	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 12:18
7	61	(((high adj breakdown) and (low adj breakdown)) and mosfet) and impurities	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 12:28
8	391	impurities near drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 12:29
9	2	(((high adj breakdown) and (low adj breakdown)) and mosfet) and (impurities near drain)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 12:36
10	45	impurities near sub	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 12:36
11	1	(impurities near sub) and (((high adj breakdown) and (low adj breakdown)) and mosfet)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 12:40
12	1535	impurities same sub	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 12:41

13	1	((high adj breakdown) and (low adj breakdown)) and mosfet) and (impurities same sub)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:02
14	132995	low adj voltage	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:03
15	236807	high adj voltage	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:03
16	57393	(low adj voltage) and (high adj voltage)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:03
17	4911	((low adj voltage) and (high adj voltage)) and MOSFET	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:04
18	398	((low adj voltage) and (high adj voltage)) and MOSFET) and impurities	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:05
19	2	((low adj voltage) and (high adj voltage)) and MOSFET) and (impurities same sub)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:06
20	383	((low adj voltage) and (high adj voltage)) and MOSFET) and impurities) and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:06
21	366	((low adj voltage) and (high adj voltage)) and MOSFET) and impurities) and substrate) and drain	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 13:07
22	145	((low adj voltage) and (high adj voltage)) and MOSFET) and impurities) and substrate) and drain) and diffused	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:05
23	287	impurities same sup	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:06
24	0	((low adj voltage) and (high adj voltage)) and MOSFET) and impurities) and substrate) and drain) and (impurities same sup)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/15 14:06